Abstract

Heterostructure field effect transistors (HFETs) are based on AlGaN/GaN heterostructures which offer excellent electronic properties for the development of faster, heat-resistant, energy efficient transistors and application in microwave-power amplifiers [1,2]. The outstanding device performance in cut-off frequency, breakdown voltage, and device output power [3,4]. However, the comparatively analysis of small signal and large signal parameters which are seldom found in this paper.

References
Comparative Analysis of Small Signal and Large Signal parameters in Heterostructure Field Effect Transistors


Index Terms

Computer Science
Signal Processing
Keywords
Hfets  Organic Chemical Vapor Deposition (mocvd)  Two-dimensional Electron Gas
(2deg)  E-mode (enhancement)
Mode)  D-mode (depletion
Mode)